

DALLAS

SEMICONDUCTOR

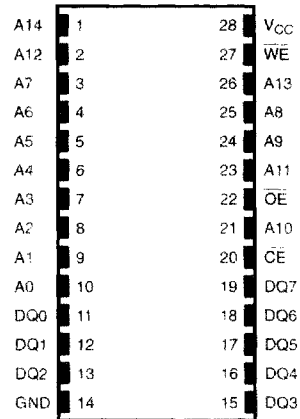
DS1230Y/AB

256K Nonvolatile SRAM

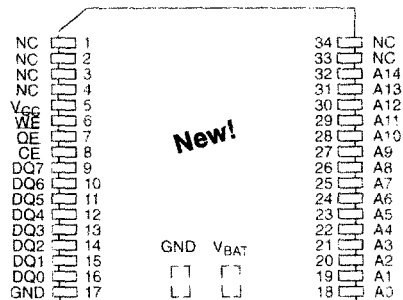
FEATURES

- 10 years minimum data retention in the absence of external power
- Data is automatically protected during power loss
- Replaces 32K x 8 volatile static RAM, EEPROM or Flash memory
- Unlimited write cycles
- Low-power CMOS
- Read and write access times as fast as 70 ns
- Lithium energy source is electrically disconnected to retain freshness until power is applied for the first time
- Full $\pm 10\%$ V_{CC} operating range (DS1230Y)
- Optional $\pm 5\%$ V_{CC} operating range (DS1230AB)
- Optional industrial temperature range of -40°C to $+85^{\circ}\text{C}$, designated IND
- JEDEC standard 28-pin DIP package
- New PowerCap Module (PCM) package
 - Directly surface-mountable module
 - Replaceable snap-on PowerCap provides lithium backup battery
 - Standardized pinout for all nonvolatile SRAM products
 - Detachment feature on PowerCap allows easy removal using a regular screwdriver

PIN ASSIGNMENT



28-PIN ENCAPSULATED PACKAGE
740 MIL EXTENDED



34-PIN POWERCAP MODULE (PCM)
(USES DS9034PC POWERCAP)

PIN DESCRIPTION

- | | | |
|-----------------|---|------------------|
| A0 – A14 | – | Address Inputs |
| DQ0 – DQ7 | – | Data In/Data Out |
| \overline{CE} | – | Chip Enable |
| \overline{WE} | – | Write Enable |
| \overline{OE} | – | Output Enable |
| V_{CC} | – | Power (+5V) |
| GND | – | Ground |
| NC | – | No Connect |